DO NOT ENTER JWD 10/18/06

REMARKS

All of the claims submitted for examination in this application have been rejected on four substantative grounds. Applicants have reviewed these grounds of rejection and respectfully submit that all of the claims currently in the application are patentable thereover.

The first substantive ground of rejection is directed to Claims 1-13. Claims 1-13 stand rejected, under 35 U.S.C. §103(a), as being unpatentable over U.S. Patent Application Publication No. US 2002/0052125 A1 to Shaffer, II et al. taken in view of U.S. Patent No. 6,121,130 to Chua et al. and in further view of U.S. Patent No. 5,908,510 to McCullough et al.

The principal Shaffer, II et al. application discloses a process for forming an etched, coated semiconductor device followed by removing impurities comprising disposing a low dielectric constant curable organic polymeric film, generally as a multi-layer film on an electrically-conductive surface of a semiconductor substrate device, curing the film layers and contacting the film layer with heat, in a baking step, to remove impurities from the film and the device.

The Official Action admits that the claims of the present application differ from the Shaffer, II et al. disclosure by the requirement that the cured polymeric organic film be contacted with supercritical carbon dioxide. In view of this failing, the Official Action applies Chua et al. for its teaching of removing both residual solvent and polymerization by-products from a semiconductor substrate coated with a film by thermal steps and McCullough et al. for its disclosure of removing residue from semiconductor devices that may include both etched and patterned composites having both silicon and polymeric layers by contact with supercritical carbon dioxide, the contact generally being at a significantly elevated temperature.